

Title (en)

CONDUCTOR-INSULATOR SEMICONDUCTOR DEVICES AND METHODS FOR MAKING THE SAME.

Title (de)

LEITER-ISOLATOR-HALBLEITERVORRICHTUNGEN UND VERFAHREN ZUR HERSTELLUNG.

Title (fr)

DISPOSITIFS CONDUCTEUR-ISOLANT-SEMICONDUCTEUR ET LEUR PROCEDE DE FABRICATION.

Publication

EP 0039736 A4 19830406 (EN)

Application

EP 80902383 A 19801112

Priority

US 9412179 A 19791114

Abstract (en)

[origin: WO8101485A1] A pair of narrow channel IGFET devices (10A, 10B) having separate insulated gate electrode structures (19A, 19B) formed over narrow channel regions (28A, 28B) of a substrate (11) flanking a central enhancement region (27). Methods of forming the narrow channel regions using a single photolithography step and forming separate gate electrode structures overlying each using alternative processes, each generally involving two photolithography steps, are set forth.

IPC 1-7

H01L 29/78; **H01L 27/02**; **H01L 29/34**; **H01L 29/06**; **H01G 7/00**; **B44C 1/22**

IPC 8 full level

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Citation (search report)

- DE 2911726 A1 19791011 - NCR CO
- FR 2137592 A1 19721229 - MATSUSHITA ELECTRIC IND CO LTD
- FR 2321194 A1 19770311 - NIPPON TELEGRAPH & TELEPHONE [JP]
- US 4033026 A 19770705 - PASHLEY RICHARD D

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DOCDB simple family (publication)

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